



**National Semiconductor**  
**Memory Systems**

**BLC 0512**

**TECHNICAL MANUAL**

This document, and all subject matter disclosed herein, are proprietary items to which National Semiconductor Corporation retains the exclusive rights of dissemination, reproduction, manufacture, and sale. This document is submitted in confidence for consideration by the designated recipient or intended using organization alone, unless permission for further disclosure is expressly granted in writing by National Semiconductor Corporation.



**National Semiconductor  
Memory Systems**

MULTIBUS is a trademark of Intel Corporation

Copyright (C) 1981 National Semiconductor Corporation

420109405 REV A  
October 1981

## CONTENTS

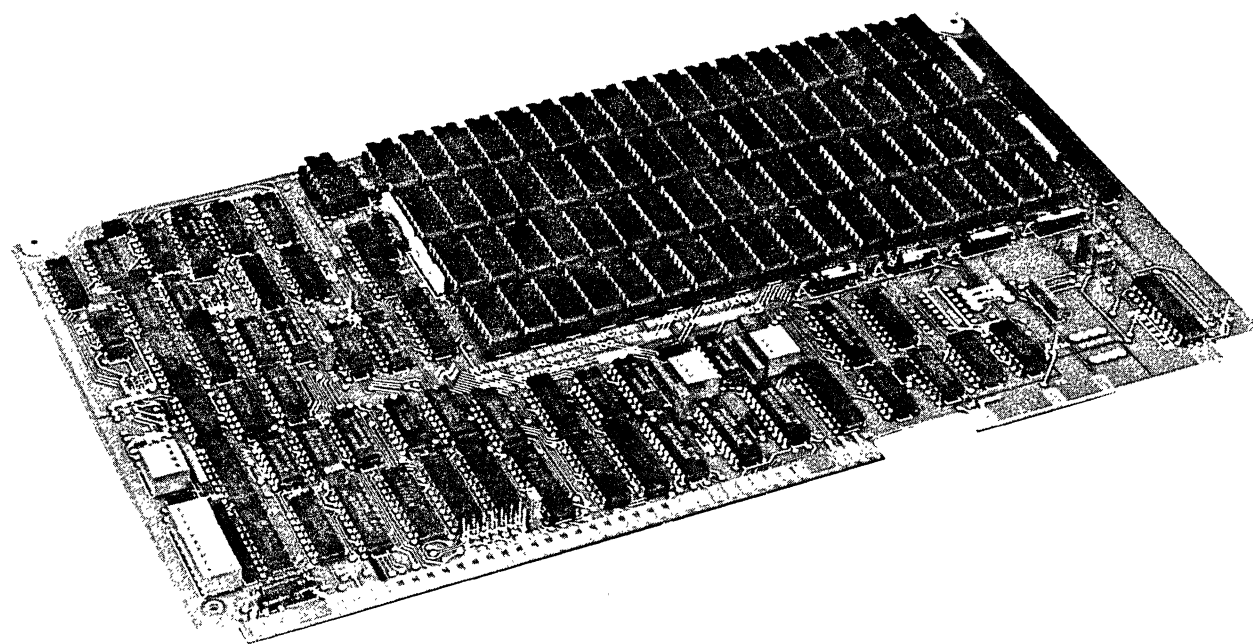
Chapter		Page
1.	GENERAL DESCRIPTION	1-1
1.1	INTRODUCTION . . . . .	1-1
1.2	PHYSICAL DESCRIPTION . . . . .	1-1
1.3	POWER REQUIREMENTS . . . . .	1-1
1.4	ACCESS AND CYCLE TIME . . . . .	1-2
1.5	OPTIONS . . . . .	1-2
1.6	RELIABILITY . . . . .	1-3
2.	SPECIFICATIONS	2-1
2.1	INTRODUCTION . . . . .	2-1
2.2	ENVIRONMENTAL SPECIFICATIONS . . . . .	2-1
2.3	ELECTRICAL SPECIFICATIONS . . . . .	2-3
3.	THEORY OF OPERATION	3-1
3.1	INTRODUCTION . . . . .	3-1
3.2	INTERFACE . . . . .	3-1
3.3	ADDRESSING . . . . .	3-8
3.4	DATA AND PARITY . . . . .	3-8
3.5	CONTROL AND STATUS REGISTER . . . . .	3-9
3.6	ARBITRATION . . . . .	3-10
3.7	TIMING AND CONTROL . . . . .	3-11
4.	INSTALLATION AND MAINTENANCE	4-1
4.1	INTRODUCTION . . . . .	4-1
4.2	TOOLS REQUIRED . . . . .	4-1
4.3	UNPACKING AND INSPECTION . . . . .	4-1
4.4	BACKPLANES . . . . .	4-1
4.5	PROCESSORS . . . . .	4-2
4.6	POWER CONSIDERATION AND BATTERY BACKUP . . . . .	4-3
4.7	ADDRESS RANGE SELECTION . . . . .	4-3
4.8	MEMORY SIZE SELECTION . . . . .	4-4
4.9	CSR ADDRESS SELECTION . . . . .	4-7
4.10	SELECTABLE INTERRUPTS . . . . .	4-8
4.11	ADVANCED ACKNOWLEDGE . . . . .	4-9
4.12	INTERNAL/EXTERNAL REFRESH . . . . .	4-9
4.13	INSTALLING MEMORY MODULES . . . . .	4-9
4.14	VERIFYING MEMORY OPERATION . . . . .	4-10
4.15	MAINTENANCE . . . . .	4-10
4.16	TROUBLESHOOTING . . . . .	4-10
5.	COMPATIBLE EQUIPMENT	5-1
5.1	INTRODUCTION . . . . .	5-1
5.2	BACKPLANES . . . . .	5-1
5.3	OTHER MODULES . . . . .	5-1
6.	APPENDIX A REFERENCE DOCUMENTS	6-1

## FIGURES

Figure	Page
2.1 Memory Read Timing . . . . .	2-5
2.2 Memory write Timing . . . . .	2-5
2.3 I/O Read Timing . . . . .	2-6
2.4 I/O write Timing . . . . .	2-6
3.1 External Refresh . . . . .	3-8

## TABLES

Table	Page
2.1 Driver and Receiver Characteristics . . . . .	2-3
2.2 Timing Parameters . . . . .	2-7
3.1 Pin Assignment Connector P1 . . . . .	3-2
3.1 Pin Assignment Connector (Cont.) . . . . .	3-3
3.2 Connector Pin Assignments . . . . .	3-4
3.3 Data Transfer Modes . . . . .	3-5
4.1 Jumper Definitions . . . . .	4-2
4.2 Power Jumpers . . . . .	4-3
4.3 Power Requirements . . . . .	4-3
4.4 Starting Address Select . . . . .	4-5
4.5 Addresses Bank Select . . . . .	4-6
4.6 Memory Switch Settings . . . . .	4-6
4.7 I/O Addressing . . . . .	4-7
4.8 LSB, 8-bit CSR Address Assignment . . . . .	4-7
4.9 MSB, CSR Address . . . . .	4-8
4.10 Selectable Interrupt Jumpers . . . . .	4-8
4.11 AACK Jumpers . . . . .	4-9



BLC 0512 PHOTOGRAPH

## Chapter 1

### 1.1 INTRODUCTION

The BLC 0512 memory module is an add-in memory for computers using the Multibus or BLC series computers. It is IEEE 796 BUS compatible, compliance level D16 M24 I16 V0. The flexibility of the BLC 0512 makes it compatible with a wide variety of system configurations.

### 1.2 PHYSICAL DESCRIPTION

The BLC 0512 is contained on a single four layer PC board which plugs directly into the BLC 604 or BLC 614 modular backplanes and card cages or any backplane conforming to IEEE 796 BUS specification. It has two sets of edge connectors: one 86 pin on .156 inch centers for the system bus and a 60 pin on .100 inch centers for auxiliary power and optional bus signals. The dimensions of the PC board are:

Thickness	0.062 +/- .005 inches
Width	6.750 +/- .005 inches
Length	12.00 +/- .005 inches

The maximum component height shall not exceed 0.375 inches and the maximum total thickness of the finished assembly will be less than 0.490 inches.

### 1.3 POWER REQUIREMENTS

The BLC 0512 requires only +5 vdc. Jumper points are provided to implement battery back-up.

#### 1.3.1 Parameters and Conditions

The BLC 0512 requires the following voltages at the specified current:

Voltage	Standby		Operating	
	Maximum	Typical	Maximum	Typical
+5v +/- 5%	3.0	2.8	3.1	2.9

### 1.3.2 Battery Back-up Voltage Requirements

The battery back-up (protected) voltages must meet the following requirements:

1. +5v +/- 5%            a1.5A

### 1.4 ACCESS AND CYCLE TIMES

The performance of the BLC 0512 memory card is as follows:

Function	Access Time (maximum)	Cycle Time (maximum)	Notes
Memory Read	275 ns	400 ns	1,2,3
Memory Write	110 ns	400 ns	1,2,3
I/O Read	90 ns	150 ns	2,3
I/O Write	90 ns	150 ns	2,3

- Notes:
1. If a memory operation is requested during a refresh cycle, a delay of up to 500 ns can be added to access and cycle time.
  2. Read access is defined as MRDC\* or IORC\* asserted to XACK\* asserted. Write cycle access time is defined as MWTC\* or IOWC\* asserted to XACK\* asserted
  3. Cycle time is defined as command asserted to internal busy negated.

### 1.5 OPTIONS

The BLC 0512 is available with a variety of options to enhance the card.

#### 1.5.1 Memory Capacity

The standard capacity of the BLC 0512 is 524,288 bytes by 9 bits (512K x 9). Optional capacities are available from a minimum of 131,072 bytes by 8 bits to a maximum of 524,288 bytes by 9 bits in increments of 131,072 by 8 or 9 bits.

### 1.5.2 Parity Generation and Check

The BLC 0512 is available with or without the parity option. This option includes parity storage, parity generation and checking and a special software addressable register for controlling the parity and interrupt functions and logging the location of parity errors. The on-board register will be referred to as the CSR (Control and Status Register). Refer to Sections 3.4 and 3.5 for details of parity operation and the CSR.

### 1.5.3 Refresh

The standard configuration of the BLC 0512 is with internally controlled, transparent refresh. The external refresh option, if selected, may be used as either synchronous or asynchronous refresh input.

### 1.5.4 Advanced Acknowledge

Advanced Acknowledge (AACK\*) can be jumper selected to one of three different times to enhance system performance, or a jumper can be removed to completely isolate AACK\* from the interface.

### 1.5.5 Battery Back-up

Battery or protected voltages may be supplied via the P2 connector to protect against data loss when unprotected power supplies are out of tolerance. In the battery back-up mode circuitry on the BLC 0512 that is necessary to maintain data is kept operational but external cycles may not be performed.

## 1.6 RELIABILITY

The BLC 0512 was designed and built to the best commercial standards of workmanship. Vigorous testing is conducted (including testing over the operating temperature and voltage ranges) to ensure reliable service of 10 years at 24 hours per day. To further enhance reliability, only pre-conditioned parts are used (National's A+ conditioning or equivalent).



## Chapter 2

### SPECIFICATIONS

#### 2.1 INTRODUCTION

This chapter describes the operating environment and electrical specifications of the BLC 0512.

#### 2.2 ENVIRONMENTAL SPECIFICATIONS

The BLC 0512 was designed to operate over a wide range of environmental conditions. Listed below are the environmental specifications:

##### 2.2.1 Operating Specifications

- o Temperature . . . Ambient air temperature  
range of 0° C to +55° C
- o Thermal Shock . . . No greater than 30° C  
per hour.
- o Humidity . . . . . 0% to 95% relative humidity  
without condensation.
- o Altitude . . . . . -1000 feet msl to +10,000  
feet msl.
- o Cooling . . . . . Suggested minimum air flow  
of 25 cfm.

##### 2.2.2 Shipping and Storage Specifications

- o Temperature . . . . . -40° C to +85° C.
- o Thermal Shock . . . . . Not greater than 10° C per  
minute.
- o Altitude . . . . . A shipping altitude of 40,000  
feet msl can be withstood.

- o Mechanical Shock      The BLC 0512, housed in its shipping container, can tolerate mechanical shock resulting from drop tests performed in accordance with MIL-STD-810B, Method 516, Procedure V, without exhibiting damage or degradation.

### 2.3 ELECTRICAL SPECIFICATIONS

This section contains information regarding logic states, signal levels, bus timing and receiver/driver characteristics.

#### 2.3.1 Logic States

The signal name will indicate whether or not a signal is active high or active low. If the signal name ends with an asterisk, it indicates the signal is active low and its logical-electrical relationship is as follows:

Logical State	Electrical State
0	H=TTL High
1	L=TTL Low

If the signal name has no asterisk, then it is active high and its logical-electrical relationship is as follows:

Logical State	Electrical State
0	L=TTL Low
1	H=TTL High

#### 2.3.2 Driver and Receiver Characteristics

Table 2.1 lists the characteristics of the drivers and receivers used on the BLC 0512. Current levels are given in mA's.

TABLE 2.1

Signal	Type	Drivers			Receivers		
		IOL (min)	IOH (min.)	CO (max.)	ITL (max.)	ITH (max.)	CI
DATD*-DATF*	TRI	24	-15	300	-.4	20	18
ADRD*-ADR17*					-.4	20	18
MRDC*					-.4	50	18
MWTC*					-.4	50	18
IORC*					-.4	20	18
IDWC*					-.4	20	18
XACK*	TRI	24	-2.6	300			
AACK*	TRI	24	-2.6	300			
INIT*					-.4	20	18
INT0*-INT7*	O.C	60	+250 (max.)	300			
MPRO*					-.4	20	18
INH1*					-.4	20	18
M1					-.4	20	18

### 2.3.3 Bus Logic Levels

Signals used on the bus that the BLC 0512 interfaces to should meet the following requirements:

	At Receiver -----	At Driver -----
Voltage High	$5.25v > H > 2.0v$	$5.25 > H > 2.4v$
Voltage Low	$.8v > L > -.5v$	$.5v > L > 0v$

### 2.3.4 Bus Timing

Figures 2.1 thru 2.4 are the timing diagrams that pertain to the BLC 0512. Table 2.2 lists the parameter values.

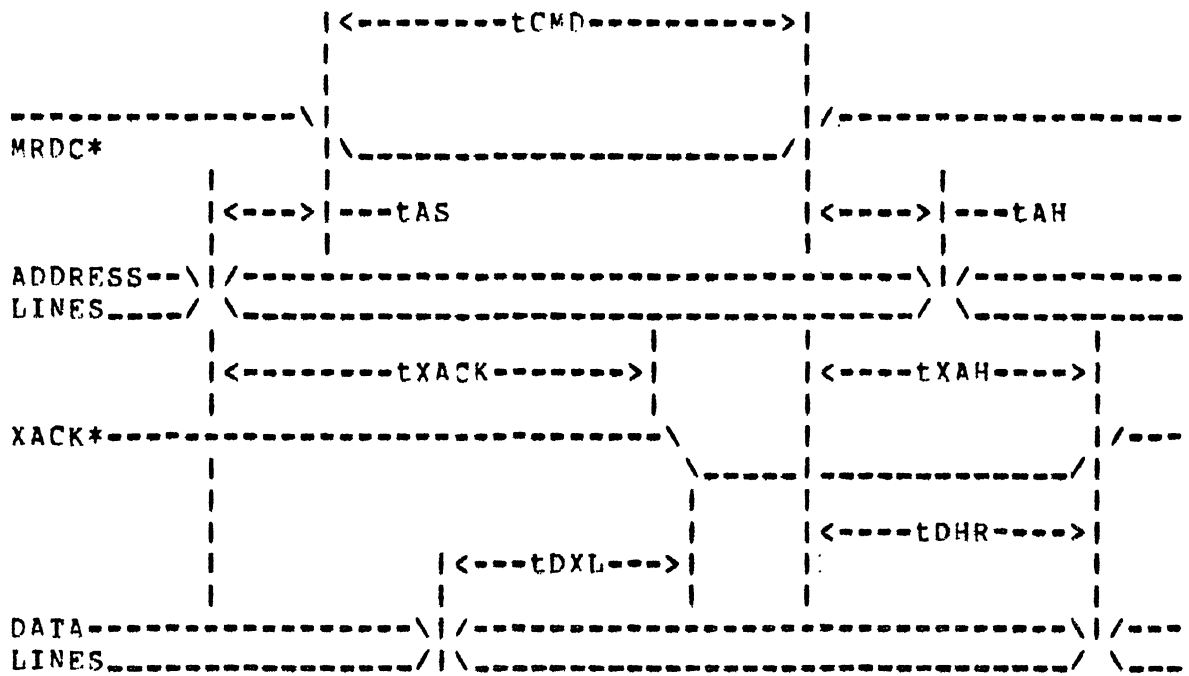


Figure 2.1 Memory Read Timing

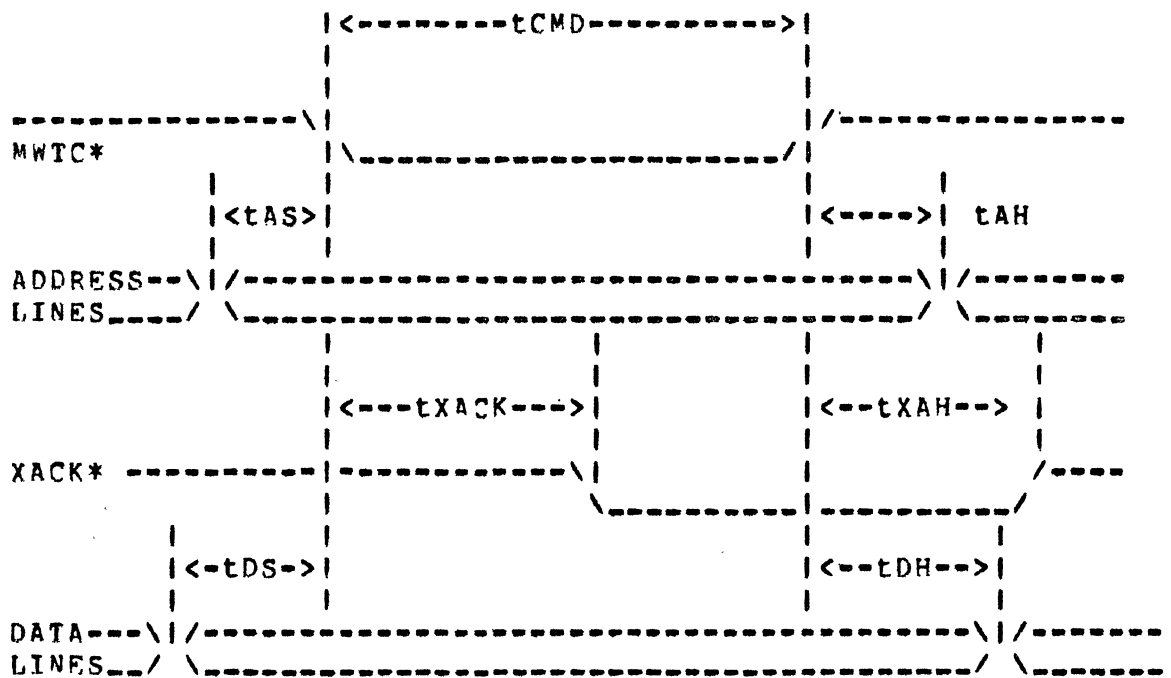


Figure 2.2 Memory Write Timing

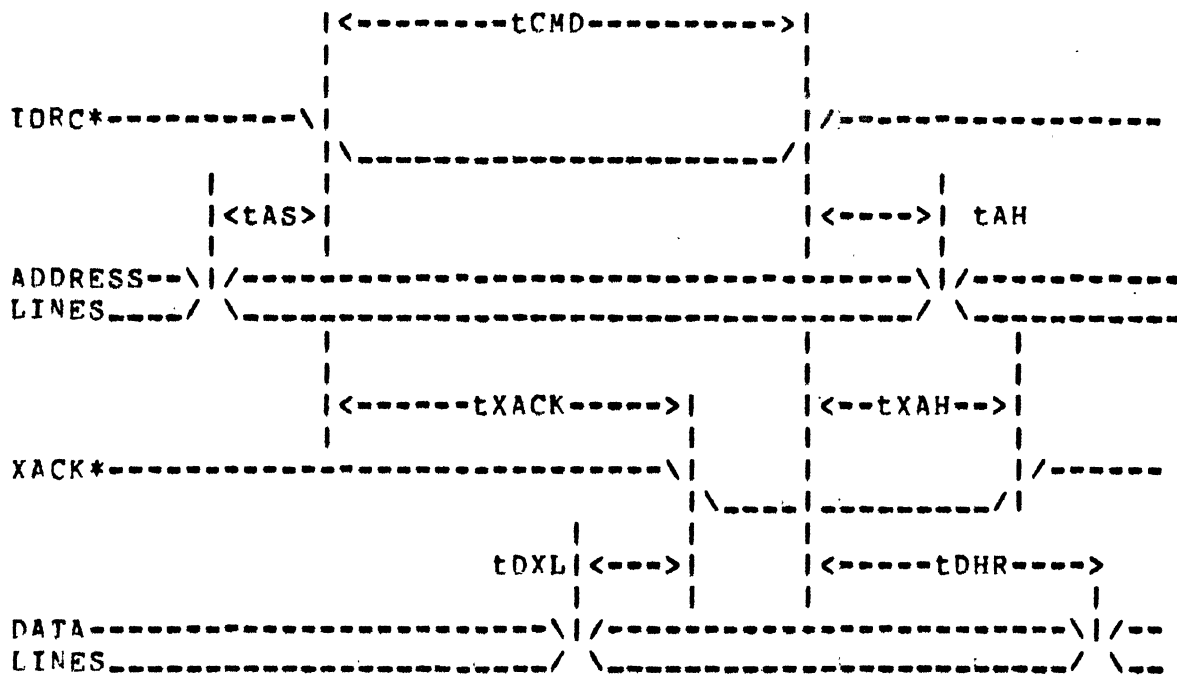


Figure 2.3 I/O Read Timing

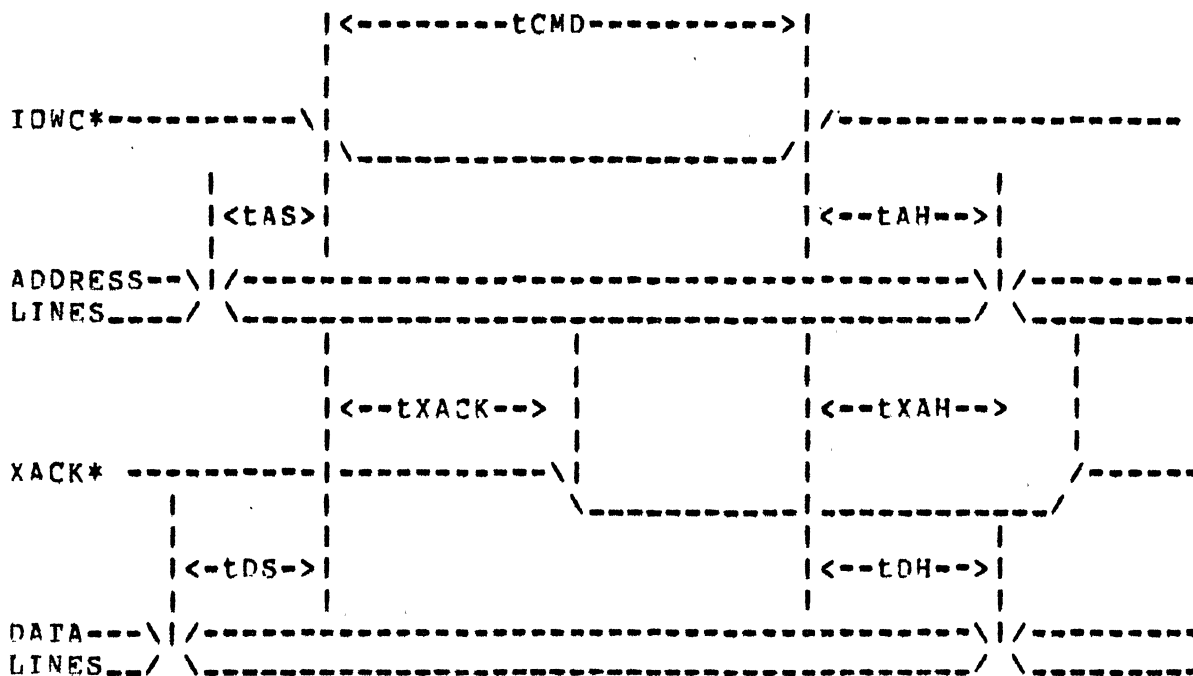


Figure 2.4 I/O Write Timing

Table 2.2 Timing Parameters

PARAMETER	MIN	MAX
tCMD	100 ns.	DC.
tAS	50 ns.	
tAH	50 ns.	
tDS	50 ns.	
tDH	50 ns.	
tXACK	0 ns.	
tXAH	0 ns.	65 ns.
tDXL	0 ns.	
tDHR		65 ns.

## Chapter 3

### THEORY OF OPERATION

#### 3.1 INTRODUCTION

This section contains a description of the interface of the BLC 0512. Signals used on the Multibus which are not used on this card are not mentioned. Tables 3.1 and 3.2 are pin listings of the BLC 0512 card edge connectors.

#### 3.2 INTERFACE

The following describes the interface of the BLC 0512. It is IEEE 796 compatible and Multibus compatible with the ability to add via jumpers other bus signals which are not standard but will not affect the operation of the bus. The signals at the interface will be divided into four basic groups: Address, Data, Control, and Non-standard.\*

- \* Non-standard refers to all signals not specified in IEEE specification 796 "Proposed Microcomputer System Bus Standard", Oct. 1980.



Table 3.1

Pin Assignment Connector P1

(Component Side)			Circuit Side			
Pin	Mnemonic	Description	Pin	Mnemonic	Description	
Power Supplies	1	GND	Signal GND	2	GND	Signal GND
	3	+5V	+5Vdc	4	+5V	+5Vdc
	5	+5V	+5Vdc	6	+5V	+5Vdc
	7			8		
	9			10		
	11	GND	Signal GND	12	GND	Signal GND
Bus Control	13			14	IVIT*	Initialize
	15	BPRN*	Bus Pri. In	16	BPRD*	Bus Pri. Out
	17			18		
	19	MRDC*	Mem Read Cmd	20	MWTC*	Mem Write Cmd.
	21	IORC*	IO Read Cmd	22	IDWC*	IO Write Cmd.
	23	XACK*	XFER Acknowledge	24	INH1*	Inhibit 1 (disable RAM)
Bus Control and Address	25			26		
	27	BHEN	Byte High Enable	28	AD10*	
	29			30	AD11*	Address Bus
	31			32	AD12*	
	33			34	AD13*	
Interrupts	35	INT6*	Parallel Interrupt Requests	36	INT7*	Parallel Interrupt Requests
	37	INT4*		38	INT5*	
	39	INT2*		40	INT3*	
	41	INT0*		42	INT1*	

Table 3.1 (Cont.)

(Component Side)			Circuit Side			
	Pin	Mnemonic Description		Pin	Mnemonic Description	
Ad- dress	43	ADRE*		44	ADRF*	
	45	ADRC*		46	ARD*	
	47	ADRA*	Address	48	ADRB*	Address
	49	ADR8*	Bus	50	ADR9*	Bus
	51	ADR6*		52	ADR7*	
	53	ADR4*		54	ADR5*	
	55	ADR2*		56	ADR3*	
	57	ADR0*		58	ADR1*	
Data	59	DATE*		60	DATF*	
	61	DATC*		62	DATD*	
	63	DATA*	Data	64	DATB*	Data
	65	DAT8*	Bus	66	DAT9*	Bus
	67	DAT6*		68	DAT7*	
	69	DAT4*		70	DAT5*	
	71	DAT2*		72	DAT3*	
	73	DAT0*		74	DAT1*	
Power Sup- plies	75	GND	Signal GND	76	GND	Signal GND
	77			78		
	79			80		
	81	+5V	+5Vdc	82	+5V	+5Vdc
	83	+5V	+5Vdc	84	+5V	+5Vdc
	85	GND	Signal GND	86	GND	Signal GND

Table 3.2

Connector Pin Assignments

Pin	(Component Side)	Pin	Circuit Side
Mnemonic		Mnemonic	Description
1	GND	2	
3	+5VB	4	+5VB
5		6	
7		8	
9		10	
11		12	
13		14	
15		16	
17		18	
19		20	MPR0*
21		22	
23		24	
25		26	
27		28	
29		30	
31	EX REF	32	
33		34	
35		36	
37		38	
39		40	
41		42	
43		44	
45		46	
47		48	
49		50	
51		52	
53		54	
55	ADR16*	56	ADR17*
57	ADR14*	58	ADR15*
59		60	

### 3.2.1 Address and Inhibit Lines

The address and inhibit lines are comprised of the following signals:

Address	ADRO* thru ADR17*
Byte High Enable	BHEN*
Inhibit	INH1*

#### 3.2.1.1 Address (ADRO\* - ADR17\*)

These 24 lines are used to specify a memory location out of 16 megabytes if all 24 lines are used or 1 megabyte if 20 lines are used. Either 8 or 16 of these lines are used to specify an I/O address that will enable access to the onboard CSR (Port address).

#### 3.2.1.2 Byte High Enable (BHEN\*)

BHEN\*, when asserted enables the upper byte (8-F) onto the data bus.

#### 3.2.1.3 Inhibit 1 (INH1\*)

When INH1\* is asserted no later than 50 nanoseconds after MRDC\* or M#TC\*, the memory will be disabled from driving any signals active on the bus and will be inhibited from performing any write cycles.

### 3.2.2 Data Lines

The data lines are comprised of the following signals:

Data	DAT0* - DATF*
------	---------------

These 16 lines provide data to the memory during a write and are driven by the memory during a memory read. If BHEN\* is not asserted, the lower 8 lines are used (DAT0\* - DAT7\*) to do byte transfers only. If BHEN\* is asserted, and ADRO\* is not asserted, all 16 data lines are used. If both BHEN\* and ADRO\* are asserted, only the upper 8 bits (DAT8\*-DATF\*) are used. Table 3.3 shows the different data transfer modes.

Table 3.3

DATA TRANSFER MODES		
BHEN*	ADRO*	FUNCTION
0	0	Transfer lower (even) byte on DAT0*-DAT7*
0	1	Transfer high (odd) byte on DAT0*-DAT7*
1	0	Transfer 16 bit word on DAT0-DATF*
1	1	Transfer high (odd) byte on DAT8*-DATF*

### 3.2.3 Control Lines

The control lines are comprised of the following signals:

Interrupt Requests	INT0* - INT7*
Bus Priority	BPRN* - BPRO*
Initialize	IVIT*
Memory Read Command	MRDC*
Memory write Command	MWTC*
I/O Read Command	IORC*
I/O Write Command	IDWC*
Transfer Acknowledge	XACK*

#### 3.2.3.1 Memory Read Command (MRDC\*)

MRDC\* indicates that a memory read cycle is to be performed and an address is valid on ADRO\* - AD17\*. The memory must respond with XACK\* and drive data on DATO\*-DATF\* within 1.5 microseconds if an in-range address was present at the leading edge of MRDC\*. Refer to Figure 2.1 for memory read timing.

#### 3.2.3.2 Memory Write Command (MWTC\*)

MWTC\* is an indication to the memory that a valid address and data are on the bus and a write cycle is to be performed if an in-range address was present at the leading edge of MWTC\*. If an in-range address was present, the memory must respond with XACK\* within 1.5 microseconds. Refer to Figure 2.2 for memory write timing.

#### 3.2.3.3 I/O Read Command (IORC\*)

IORC\* is an indication to the CSR that a valid address is present on ADRO\* - ADRF\* if 16 bit addressing is selected or on ADRO\* - ADR7\* if 8 bit I/O addressing is selected. If the address matches that of the on board CSR, it must respond within 1.5 microseconds by asserting XACK\* and driving the data lines. Either 8 bit or 16 bit data transfers may be performed. Refer to Figure 2.3 for I/O read timing.

#### 3.2.3.4 I/O write Command (IDWC\*)

IDWC\* is an indication to the CSR that valid addresses and data are on the bus (8 or 16 bit address or data). If the address matches that of the CSR it must respond with XACK\* within 1.5 microseconds and write those bits in the CSR which may be written (Bits 4 thru 15 are read only bits.) Refer to Figure 2.4 for I/O write timing.

### 3.2.3.5 Transfer Acknowledge (XACK\*)

The BLC 0512 will respond with XACK\* whenever an in-range address was present during the leading edge of a command signal. It will not be asserted until the BLC 0512 is ready to release the bus on a write cycle or data is valid on the bus during a read cycle.

### 3.2.3.6 Initialize (INIT\*)

INIT\* will clear bits 0-3 in the CSR, and clear the interrupt flip flop.

### 3.2.3.7 Interrupt Requests (INT0\* - INT7\*)

One of eight interrupt requests may be jumper selected on the BLC 0512. The selected interrupt request will be driven active when a parity error occurs and bit 1 in the CSR, (enable parity reporting) is set to a 1. The BLC 0512 will accommodate non-bus vectored interrupts only. The interrupt request will be cleared when an I/O write is performed writing a zero into bits 2 or 3 (parity error byte 0 byte 1) of the CSR, or INIT\* is asserted.

### 3.2.3.8 Bus Priority (BPRN\*, BPRO\*)

The bus priority signals are not used or driven by the BLC 0512. They are jumpered together on the memory to maintain the bus priority daisy chain.

## 3.2.4 Non Standard Signals

This special group of signals may be connected to the interface via jumpers if desired. Normally, they are not connected. The signals in this group are:

Advanced Acknowledge	AACK*
External Refresh	M1*

### 3.2.4.1 Advanced Acknowledge

Advanced Acknowledge can be jumper selected at one of three different timing taps referenced to setting the Read/Write flip flop. If the use of AACK\* is not desired, it may be isolated from the interface connector by removing a jumper. AACK\* will only be asserted on memory read or write cycles.

### 3.2.4.2 External Refresh M1\*

M1\* can be used as either a synchronous or an asynchronous refresh input. Refer to Figure 3.1 for external refresh timing.

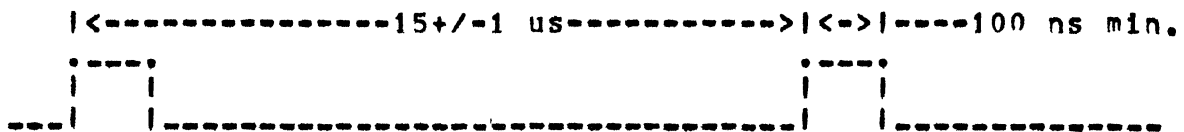


Figure 3.1 External Refresh

## 3.3 ADDRESSING

The BLC 0512 will operate with either 20 or 24 bit memory addressing. Addresses ADR1\* - ADR13\* are received by 74LS533 bus receiver/latches. ADR14\* - ADR17\* are received by 74LS244 bus receivers and then routed to 74LS533's to be latched. The latched outputs of ADR1\* - ADR17 are routed to multiplexers to generate the RAM addresses, to the CSR address selection logic, the CSR error address latch, and the memory selection logic. The outputs of the multiplexers are wire-ORed with the RAM refresh addresses and then routed to a MOS driver for driving the RAM array. If a CSR cycle is to be performed, the CSR address selection logic will generate a -SELIO if the correct address is provided on the bus. If a memory cycle is to be performed, the memory selection logic will generate a LSEL signal if an in range address is present on the bus.

## 3.4 DATA AND PARITY

The BLC 0512 receives and drives data on a bi-directional data bus and also uses a common bi-directional data bus internally. Refer to Figure 3.2 for a block diagram of the data flow. There are four basic components attached to the internal data bus, the bus transceivers which receive data from and transmit data to the system data bus, the data latches which latch data into and from the memory, parity generator/checkers, and the RAM array.

The bus transceivers are 74LS640 octal bus transceivers with the "A" side connected to the system bus and the "B" side connected to the internal bus. Three of these devices are used. One for the lower byte, one for the upper byte and one is used to "swap" the upper byte internal bus to the lower byte system bus.

The data latches are 74LS373 octal transparent latches with three state outputs. The same device is used to latch data into and from the memory. Therefore, both the D inputs and Q outputs are connected to the internal bus. On both read and write cycles the latch is left "open" and the outputs in the high impedance state until data is valid on the internal bus. After data is valid the latches are enabled and the outputs turned on to the active state.

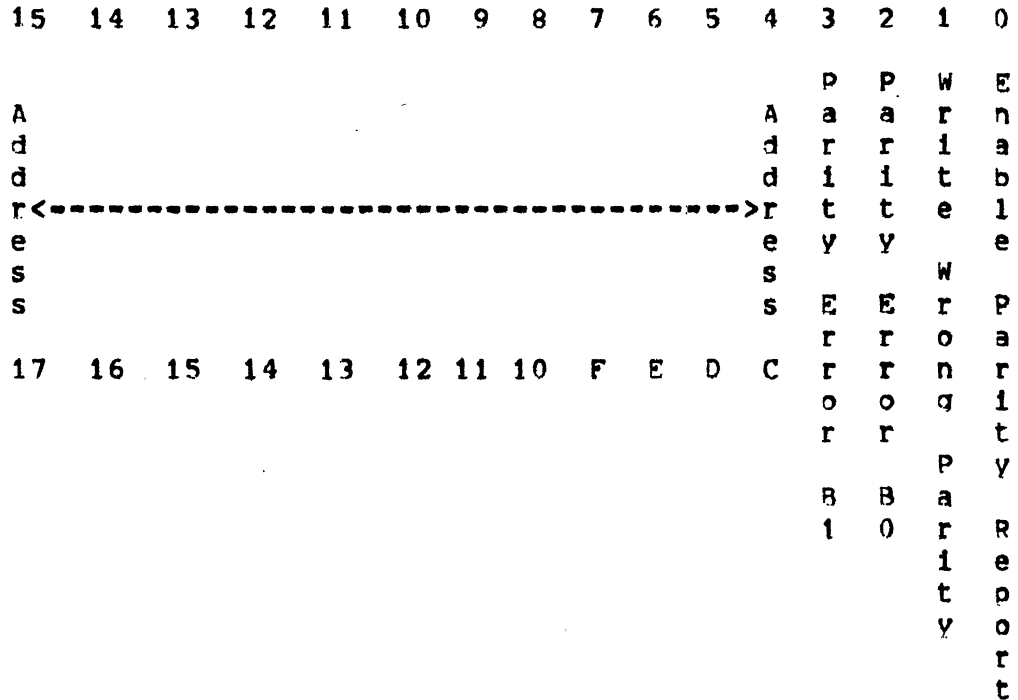
Odd parity is generated on a byte basis and stored in a ninth bit in the RAM array whenever a write cycle is performed. On a read cycle parity is generated from the stored data and compared with the stored parity bit. The result is checked to verify no parity or data errors have occurred. Nine-bit parity generation chips are used, one connected to the upper internal data bus and the other to the lower internal data bus. Both are 74S280's. Additional circuitry is used to control the ninth bit for read and write cycles and to force parity errors if bit 0 of the CSR (Write Wrong Parity) is set.

The RAM array is comprised of 72 64K dynamic RAM's. It is in two 9 x 256K sections, each section being 8 bit x 256K plus 1 x 256 parity storage. Whenever a read cycle is performed on the BLC 0512 a full word read is done internally and only the appropriate byte(s) are driven onto the data bus. If only one byte is written, the other byte will be received but not written into memory. If a full word is written, both bytes are written simultaneously. This is done because the RAM array is structured as a 256K x 18 bit array with only write enable (WE) being unique to each byte.

### 3.5 CONTROL AND STATUS REGISTER (CSR)

The CSR is a hardware register on the BLC 0512 that is used to log the address where a parity error has occurred, indicate which byte it occurred in and control the diagnostic mode. It is accessible as an I/O port using either 8 bit, 12 bit, or 16 bit addressing. If 8 bit addressing is used, the CSR may be assigned to one of 16 different locations in the range 0E to FE. If 12 or 16 bit addressing is used, the CSR may be assigned to one of 256 locations in the range F00E to FFFE. The CSR will respond to one word location or two consecutive byte locations. The bit assignments of the CSR are as follows:





Bit 0 - Enable Parity Report - Setting this bit to a logical 1 will enable parity reporting. INIT\* or writing a zero will clear this bit.

Bit 1 - Write Wrong Parity - Setting this bit to a logical 1 will force incorrect parity to be written. INIT\* or writing a zero will clear this bit and allow correct parity to be written.

Bits 2, 3 - Parity Error - Byte 0, 1 - Read/Write bits set to a logical one when a parity error occurs in the respective byte. They are cleared by writing a logical zero or INIT\*.

Bits 4-15 - Address C thru Address 17. Read only bits. These bits will store the most significant 12 bits of the address location where the most recent parity error has occurred. These bits cannot be cleared or written.

### 3.6 ARBITRATION

The purpose of arbitration logic on the BLC 0512 is to resolve conflicts between cycles requested by the system bus and refresh cycle requests which are generated internally. Only memory read or write cycles go through the arbitration logic. I/O reads or writes are not arbitrated since they do not require any access to the RAM array. Figure 3.8 is a simplified logic diagram of the arbitration logic. The system cycle request follows a path with minimal time delays, whereas the refresh request follows a path with greater time delays. If a refresh cycle is requested prior to a bus cycle, the bus cycle will be held off by gate 1 until the refresh cycle is completed.

If the bus cycle request is asserted prior to a refresh request, the refresh request will be held off by gate 2 until the bus cycle is complete. If both cycles are requested at about the same time, the bus cycle will be given priority and the refresh request will be blocked at gate 2 and/or 3.

### 3.7 TIMING AND CONTROL

All timing is generated from a single delay line. Various taps from this delay line, gated with control signals from the system bus, provide all necessary timing and control to the other functional blocks of the BLC 0512.

## Chapter 4

### INSTALLATION AND MAINTENANCE

#### 4.1 INTRODUCTION

This section contains the basic information necessary to install and maintain the National Semiconductor BLC 0512 Multibus memory module. The BLC 0512 is designed to operate in a variety of configurations including 8 or 16 bit data busses, 20 or 24 bit memory addressing and 8 or 16 bit I/O addressing. Other options which can be selected are internal or external refresh, a CSR (Control and Status Register), selectable interrupts to indicate parity errors, advance acknowledge (AACK) and battery back-up. The following information describes how to install or remove each of these options. Table 4.1 provides descriptions of each jumper option.

#### 4.2 TOOLS REQUIRED

No special tools are required for installation. A ball-point pen or small stylus may be needed to set the switches mounted on the memory module.

#### 4.3 UNPACKING AND INSPECTION

Carefully unpack the memory module and visually examine it for physical shipping damage; i.e. broken, bent or dented parts.

#### CAUTION!

-----

Do not attempt to install or operate the memory module if damage is apparent.

#### 4.4 BACKPLANES

The BLC 0512 memory module is designed to operate in any standard Multibus backplane or any backplane conforming to the IEEE-796 specification. It is slot-independent but should be placed as close to the processor as possible.

## 4.5 PROCESSORS

The BLC 0512 will operate with any standard Multibus processor or processors which conform to the IEEE specification 796.

-----  
 Table 4.1 Jumper Definitions

W10-W17	I = Installing one of these jumpers connects INT0-INT7, respectively, to the interrupt flip flop on the BLC 0512.
	R = Removing these jumpers isolates the interrupt flip flop from the interface.
W18	I = BPRN* connected to BPRO* R = BPRN* isolated from BPRO*
W20, W21	I = +5 volt battery R = +5 volt standard
W22, W23	I = +5 volt standard R = +5 volt battery
W24	I = Internal Refresh R = External Refresh
W25	I = External Refresh R = Internal Refresh
W26	I = MPRO* installed R = MPRO* isolated from receiver
W29	I = 80 ns tap to AACK* R = 80 ns tap isolated from AACK*
W30	I = 50 ns tap to AACK* R = 50 ns tap isolated from AACK*
W31	I = 30 ns tap to AACK* R = 30 ns tap isolated from AACK*
W32	I = 16 Bit I/O Addressing R = 8 or 12 bit I/O Addressing
W33	I = 12 or 16 bit I/O Addressing R = 8 bit I/O Addressing
W34	I = AACK* to P1-25 R = AACK* isolated from P1-25
W35	I = CSR inhibited R = CSR on
I = Install	NOTE: All jumpers not listed are installed at the factory and should not be altered.
R = Remove	

#### 4.6 POWER CONSIDERATIONS

The BLC 0512 requires only +5 volts DC. Jumper points are provided to implement battery back-up if desired. To implement battery back up, refer to Table 4.2. Table 4.3 lists power requirements.

Table 4.2 POWER JUMPERS

VOLTAGE	INSTALL	REMOVE	AT PINS
+5VDC Standard	W22,W23	W20,W21	See Pin List
+5VDC Battery	W20,W21	W22,W23	P2-3,P2-4

Table 4.3 POWER REQUIREMENTS

VOLTAGE	CURRENT REQUIREMENT (MAX.)
+5VDC Standard	3.1A
+5VDC Battery	1.5A

#### 4.7 ADDRESS RANGE SELECTION

The BLC 0512 will accept either 20 or 24 bit memory addressing. To use 24-bit addressing, close Switch S2-1. To use 20-bit memory addressing, open Switch S2-1. To use fewer than 20 address lines, unused upper-address lines must be pulled up to a voltage high level, and the directions for 20 bit addressing must be followed.

The starting address may be set on any 16K word boundary (32K byte) in the 16 megabyte address range. The starting address is set via DIP Switch S2. Tables 4.4 and 4.5 list the required switch settings if 24 address lines are being used. In this case the starting address is the sum of the starting address in Table 4.4 and the bank address in Table 4.5.

If only 20-bit addressing is used, open Switches S2-6 thru S2-9 and use only Table 4.4 to determine the starting address.

#### 4.8 MEMORY SIZE SELECTION

The total memory capacity of the BUC 0512 can be set in 64K Byte increments from 64K to 512K Bytes. This is done via Switches S1-1 thru S1-3. Refer to Table 4.6 for appropriate switch settings.

Table 4.4 STARTING ADDRESS SELECT

0-1024K ADDRESS RANGE

MULTIBUS STARTING ADDRESS (HEX.)	MEMORY STARTING ADDRESS (K BYTE)	S2-5	S2-4	S2-3	S2-2	S2-10
000000	0KB	0	0	0	0	0
008000	32KB	0	0	0	0	C
010000	64KB	0	0	0	C	0
018000	96KB	0	0	0	C	C
020000	128KB	0	0	C	0	0
028000	160KB	0	0	C	0	C
030000	192KB	0	0	C	C	0
038000	224KB	0	0	C	C	C
040000	256KB	0	C	0	0	0
048000	288KB	0	C	0	0	C
050000	320KB	0	C	0	C	0
058000	352KB	0	C	0	C	C
060000	384KB	0	C	C	0	0
068000	416KB	0	C	C	0	C
070000	448KB	0	C	C	C	0
078000	480KB	0	C	C	C	C
080000	512KB	C	0	0	0	0
088000	544KB	C	0	0	0	C
090000	576KB	C	0	0	C	0
098000	608KB	C	0	0	C	C
0A0000	640KB	C	0	C	0	0
0A8000	672KB	C	0	C	0	C
0B0000	704KB	C	0	C	C	0
0B8000	736KB	C	0	C	C	C
0C0000	768KB	C	C	0	0	0
0C8000	800KB	C	C	0	0	C
0D0000	832KB	C	C	0	C	0
0D8000	864KB	C	C	0	C	C
0E0000	896KB	C	C	C	0	0
0E8000	928KB	C	C	C	0	0
0F0000	960KB	C	C	C	C	0
0F8000	992KB	C	C	C	C	C

\*K = 1024

0 = OPEN  
C = CLOSED

Table 4.5 ADDRESS BANK SELECT

1024K - 16,384K ADDRESS RANGE

MULTIBUS ADDRESS (HEX.)	MEMORY STARTING ADDRESS	S2-9	S2-8	S2-7	S2-6
000000	1024K*	0	0	0	0
100000	2048KB	0	0	0	C
200000	3072KB	0	0	C	0
300000	4096KB	0	0	C	C
400000	5120KB	0	C	0	0
500000	6144KB	0	C	0	C
600000	7168KB	0	C	C	0
700000	8192KB	0	C	C	C
800000	9216KB	C	0	0	0
900000	10240KB	C	0	0	C
A00000	11264KB	C	0	C	0
B00000	12288KB	C	0	C	C
C00000	13312KB	C	C	0	0
D00000	14336KB	C	C	0	C
E00000	15360KB	C	C	C	0
F00000	16384KB	C	C	C	C

K = 1024

0 = OPEN

C = CLOSED

Table 4.6

MEMORY SIZE SWITCH SETTINGS

Memory Size	Switches		
	S1-3	S1-2	S1-1
64KB	0	0	0
128KB	0	0	C
192KB	0	C	0
256KB	0	C	C
320KB	C	0	0
384KB	C	0	C
448KB	C	C	0
512KB	C	C	C

KB = 1024 Byte

0 = OPEN

C = CLOSED



## CSR ADDRESS SELECTION

The CSR may be configured to respond to either 8 bit, 12 bit or 16 bit I/O addressing. Refer to Table 4.7 for selection of I/O addressing. If 8 bit addressing is used, the CSR may be assigned to one of 16 possible word addresses. If either 12 or 16 bit addressing is used, the CSR may be assigned to one of 256 word addresses. Refer to Table 4.8 for 8 bit CSR address assignments, also use Table 4.9 if 12 or 16 bit addressing is used.

To inhibit the operation of the CSR, install jumper W35. With the CSR inhibited parity reporting via the Multibus interrupts is enabled. If parity reporting is not desired when W35 is installed, it is necessary to remove the interrupt jumpers.

I/O Addressing	JUMPERS	
	Install	Remove
8 bit	NONE	W32, W33
12 bit	W33	W32
16 bit	W32, W33	NONE

Table 4.7 I/O Addressing

CSR ADDRESS	Switch Settings			
	S3-4	S3-3	S3-2	S3-1
0E	C	C	C	C
1E	C	C	C	O
2E	C	C	O	C
2E	C	C	O	O
4E	C	O	C	C
5E	C	O	C	O
6E	C	O	O	C
7E	C	O	O	O
8E	O	C	C	C
9E	O	C	C	O
AE	O	C	O	C
BE	O	C	O	O
CE	O	O	C	C
DE	O	O	C	O
EE	O	O	O	C
FE	O	O	O	O

Table 4.8

CSR, 8-bit CSR Address Assignment

CSR ADDRESS	Switch Settings			
	S4-4	S4-3	S4-2	S4-1
F0XX	C	C	C	C
F1XX	C	C	C	0
F2XX	C	C	0	C
F3XX	C	C	0	0
F4XX	C	0	C	C
F5XX	C	0	C	0
F6XX	C	0	0	C
F7XX	C	0	0	0
F8XX	0	C	C	C
F9XX	0	C	C	0
FAXX	0	C	0	C
FBXX	0	C	0	0
FCXX	0	0	C	C
FDXX	0	0	C	0
FEXX	0	0	0	C
FFXX	0	0	0	0

Table 4.9 MSB, CSR Address

#### 4.10 SELECTABLE INTERRUPTS (INT0\* THRU INT7\*)

Jumpers maybe installed to drive an interrupt request when parity error occurs. Any one of the eight interrupt request lines INT0-INT7 may be selected. The interrupt will be generated when a parity error occurs and parity reporting is enabled via the CSR or the CSR is inhibited by installing jumper #35. See Section 3.4 and 3.5 for a complete description of parity and CSR operation. Table 4.10 lists jumpers for implementing interrupts.

Table 4.10

#### SELECTABLE INTERRUPT JUMPERS

INTERRUPT	INSTALL**
INT0*	w10
INT1*	w11
INT2*	w12
INT3*	w13
INT4*	w14
INT5*	w15
INT6*	w16
INT7*	w17

\*\* Install only one of these jumpers, all others should be removed.

#### 4.11 ADVANCE ACKNOWLEDGE (AACK\*)

Advance acknowledge can be jumper-selected at one of three different timing taps. If advance acknowledge is not used, it should be isolated from the interface connector by removing jumper W34.

Table 4.11 AACK JUMPERS

Time from Command*	INSTALL
30ns	W31
50ns	W30
80ns	W29

\* AACK will be held off if a refresh cycle is in progress. This could add up to 400ns to these times.

#### 4.12 INTERNAL/EXTERNAL REFRESH

The BLC 0512 can be operated with internal (transparent) refresh or with external refresh. To implement internal refresh, install jumper W24 and remove jumper W25. To implement external refresh, install jumper W25 and remove W24. External refresh may be from either a synchronous or an asynchronous source and will trigger on a low-to-high voltage transition at the interface. See Figure 3.1 for required refresh timing.

#### 4.13 INSTALLING MEMORY MODULES

The memory module must be inserted into the backplane with components facing Row 1. Make certain the module is firmly seated in the connector.

**CAUTION!**

-----

Do not attempt to install or remove memory modules with DC power applied to the backplane. Damage to the memory may occur.

**4.14 VERIFYING MEMORY OPERATION**

When memory modules are installed, apply DC power and verify operation by running system diagnostics; in particular, those that test the memory.

**4.15 MAINTENANCE**

The memory itself does not require routine maintenance on a regularly scheduled basis. System diagnostics should be performed from time to time to verify correct operation.

**4.16 TROUBLESHOOTING**

In the event problems are encountered:

- o Are all power supplies turned on? Verify that +5V is applied to the backplane.
- o Are the correct power jumpers installed?
- o Is the system configured properly? Verify that all modules are firmly seated.
- o Are all system cables properly installed? Check that the cables are connected at each end.

## Chapter 5

### COMPATIBLE EQUIPMENT

#### 5.1 INTRODUCTION

The BLC 0512 is designed to interface with any series 80 boards via the system bus as described in the IEEE specification 796 (P796 Bus). The following paragraphs describe the compatibility of the BLC 0512 memory module.

#### 5.2 BACKPLANES

The BLC 0512 is designed to be compatible with BLC 604/614 Modular Backplane and Cardcage or any backplane/cardcage that conforms mechanically and electrically to IEEE specification 796.

#### 5.3 OTHER MODULES

The BLC 0512 will be compatible with any other modules which are Multibus compatible and that conform completely with IEEE Specification 796.

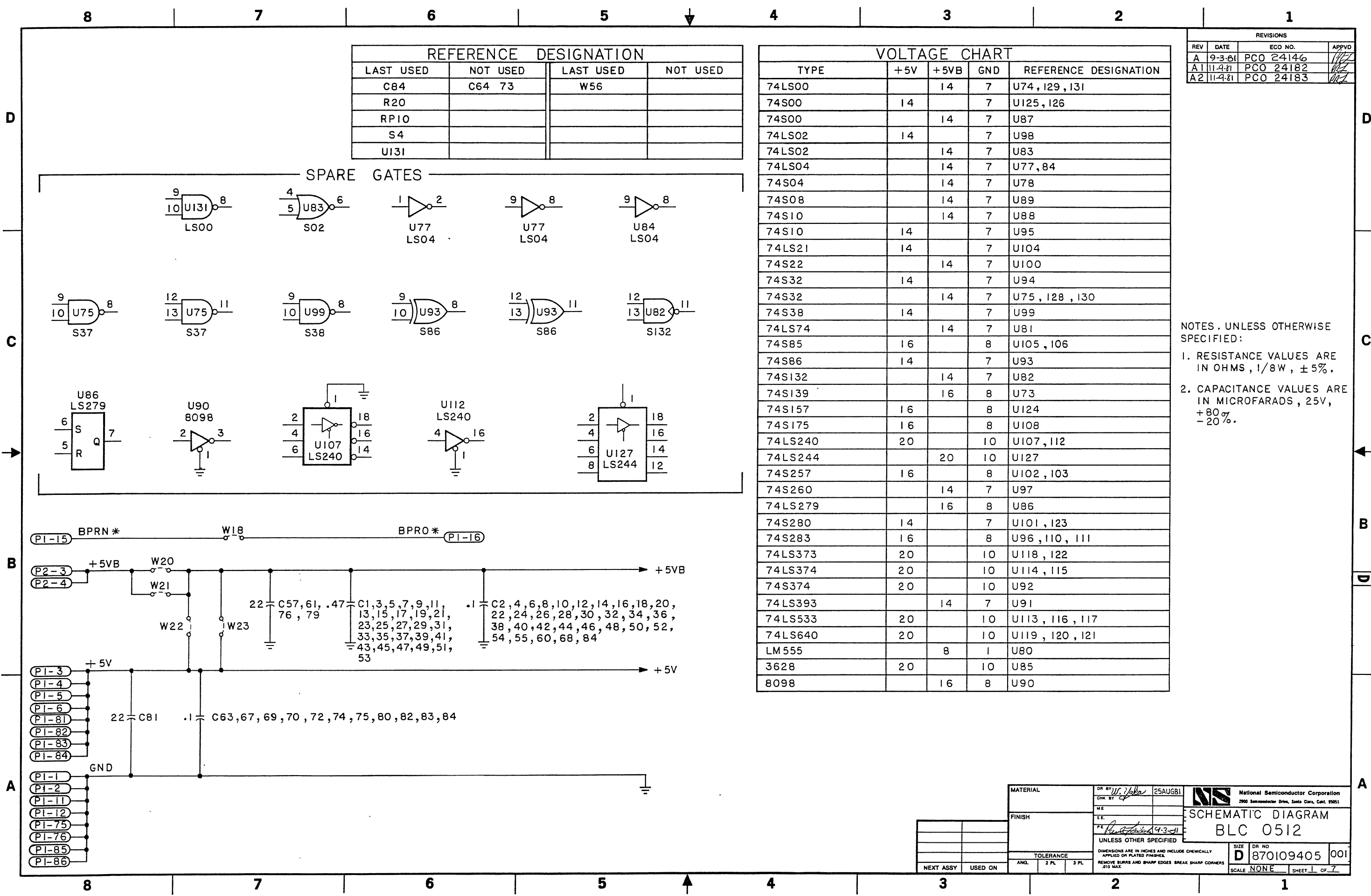
Chapter 6

APPENDIX A

This appendix contains the schematic, assembly drawing and bill of materials pertaining to the BLC 0512 memory card.

980109405    Assembly Drawing and Bill of Materials

870109405    Schematic Diagram



REFERENCE DESIGNATION			
LAST USED	NOT USED	LAST USED	NOT USED
C84	C64 73	W56	
R20			
RPI0			
S4			
UI31			

VOLTAGE CHART				
TYPE	+5V	+5VB	GND	REFERENCE DESIGNATION
74LS00		14	7	U74, 129, 131
74S00	14		7	U125, 126
74S00		14	7	U87
74LS02	14		7	U98
74LS02		14	7	U83
74LS04		14	7	U77, 84
74S04		14	7	U78
74S08		14	7	U89
74S10		14	7	U88
74S10	14		7	U95
74LS21	14		7	U104
74S22		14	7	U100
74S32	14		7	U94
74S32		14	7	U75, 128, 130
74S38	14		7	U99
74LS74		14	7	U81
74S85	16		8	U105, 106
74S86	14		7	U93
74S132		14	7	U82
74S139		16	8	U73
74S157	16		8	U124
74S175	16		8	U108
74LS240	20		10	U107, 112
74LS244		20	10	U127
74S257	16		8	U102, 103
74S260		14	7	U97
74LS279		16	8	U86
74S280	14		7	U101, 123
74S283	16		8	U96, 110, 111
74LS373	20		10	U118, 122
74LS374	20		10	U114, 115
74S374	20		10	U92
74LS393		14	7	U91
74LS533	20		10	U113, 116, 117
74LS640	20		10	U119, 120, 121
LM555		8	1	U80
3628	20		10	U85
8098		16	8	U90

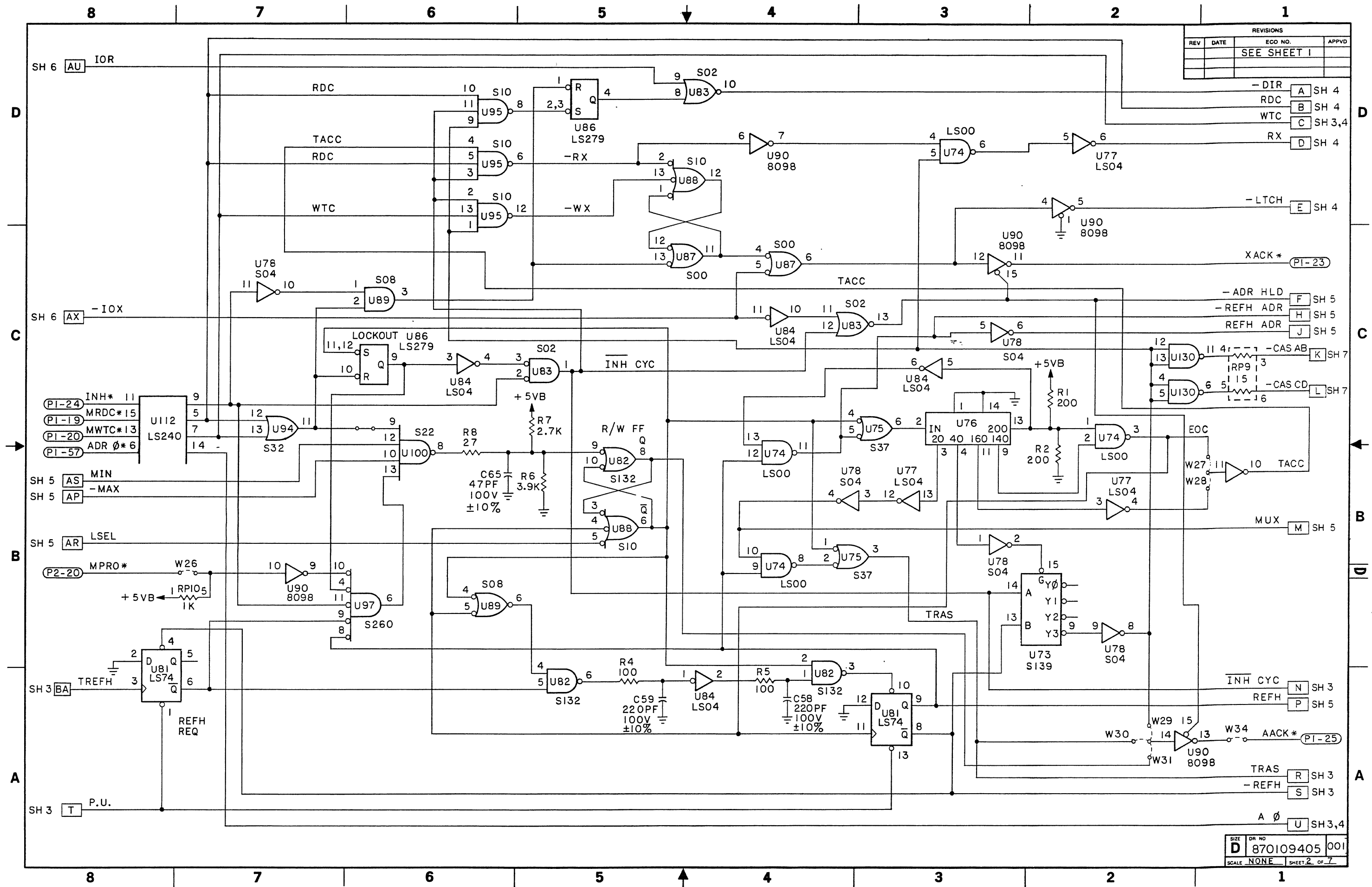
REVISIONS			
REV	DATE	ECO NO.	APPVD
A	9-3-81	PCO 24146	
A1	11-9-81	PCO 24182	
A2	11-9-81	PCO 24183	

NOTES, UNLESS OTHERWISE SPECIFIED:

1. RESISTANCE VALUES ARE IN OHMS, 1/8W, ±5%.
2. CAPACITANCE VALUES ARE IN MICROFARADS, 25V, +80% -20%.

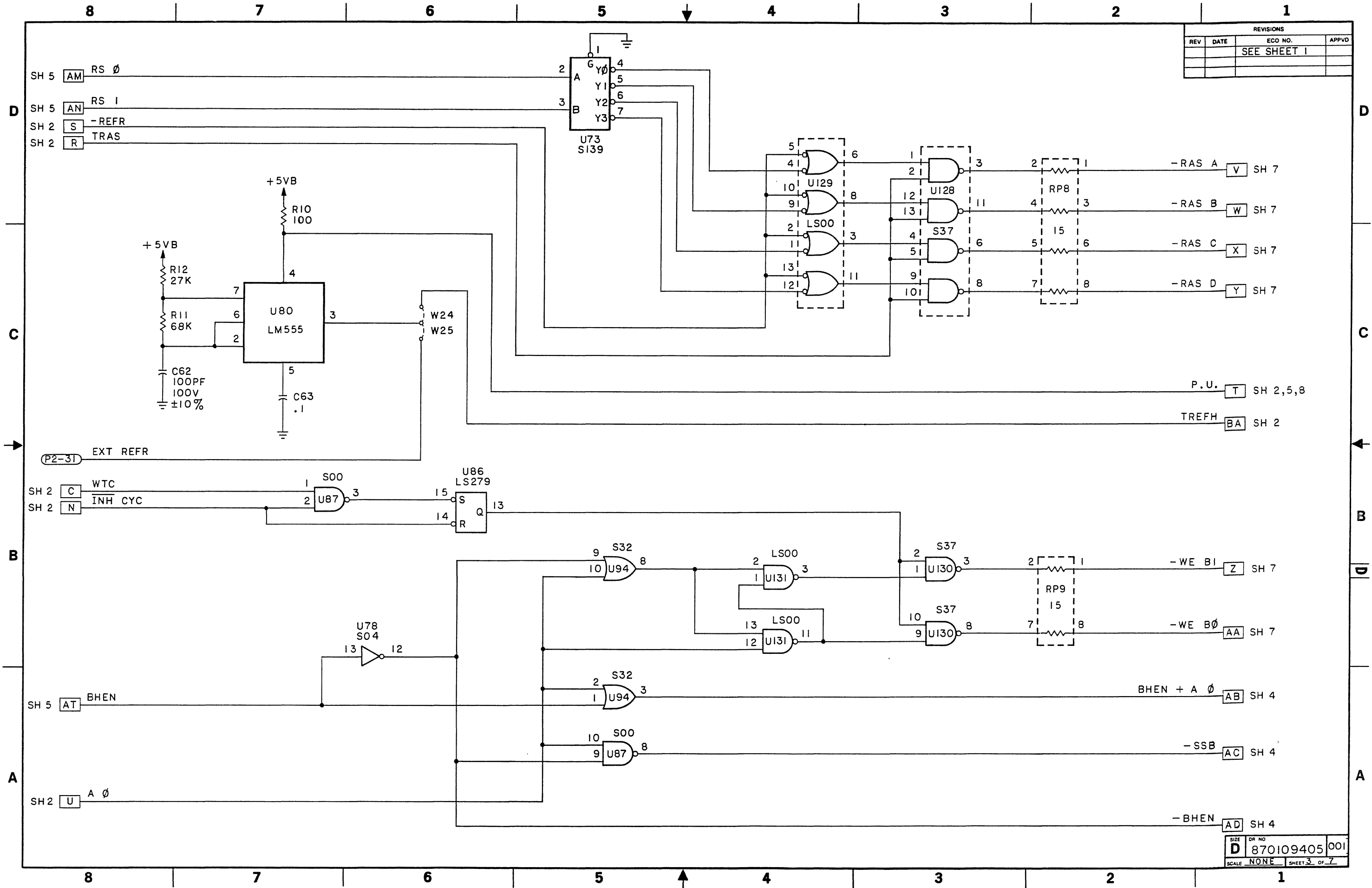
MATERIAL	DR BY <i>W. J. Jahn</i>	25AUG81	 National Semiconductor Corporation 2900 Sanson Avenue Drive, Santa Clara, Calif. 95051
FINISH	CHK BY		
TOLERANCE ANG. 2 PL 3 PL			SCHEMATIC DIAGRAM BLC 0512
DIMENSIONS ARE IN INCHES AND INCLUDE CHEMICALLY APPLIED OR PLATED FINISHES. REMOVE BURRS AND SHARP EDGES BREAK SHARP CORNERS .015 MAX.			
NEXT ASSY	USED ON	SIZE D	DR NO. 870109405 001
SCALE NONE			SHEET 1 OF 7

REVISIONS			
REV	DATE	ECO NO.	APPVD
		SEE SHEET 1	

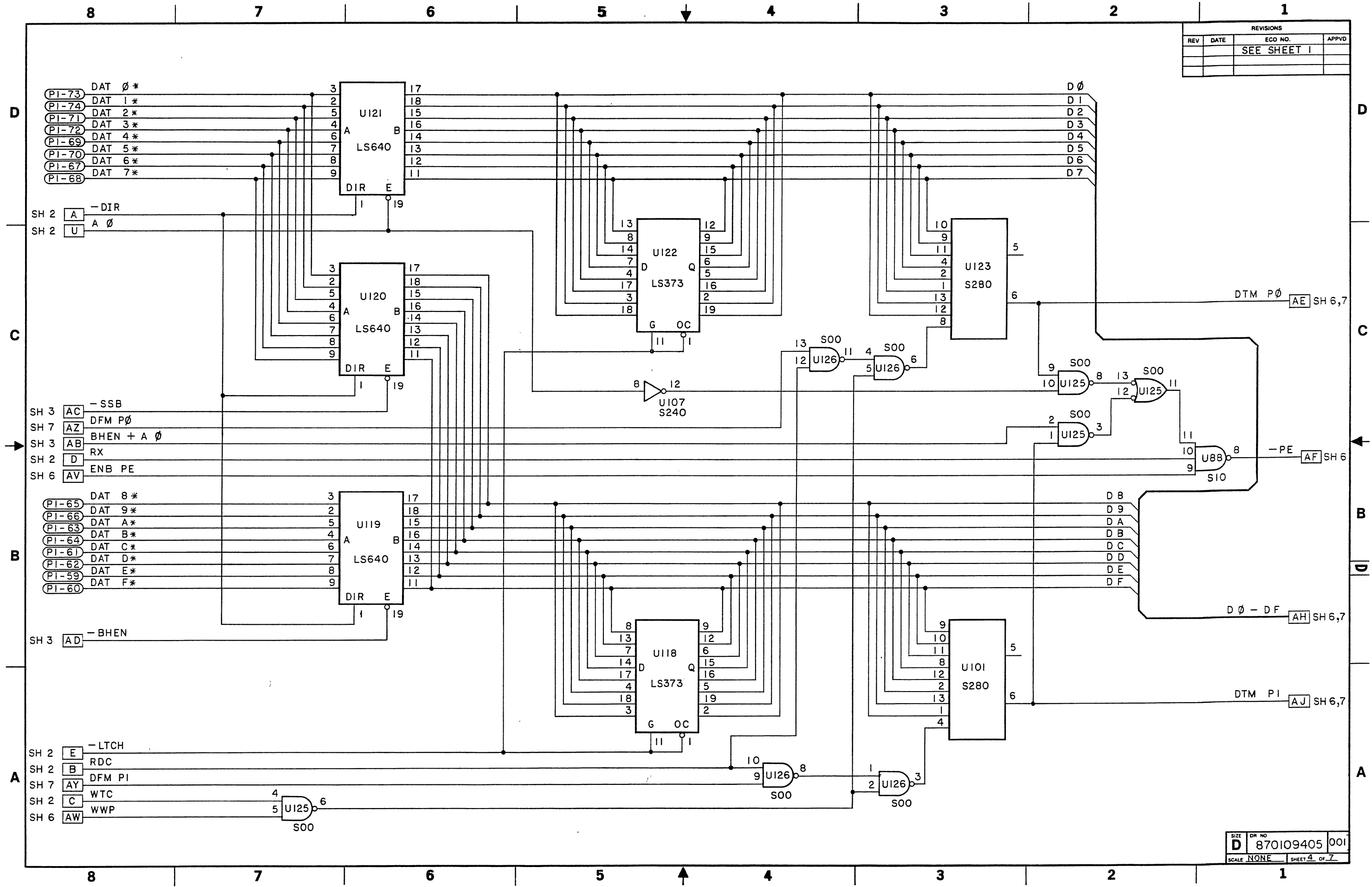




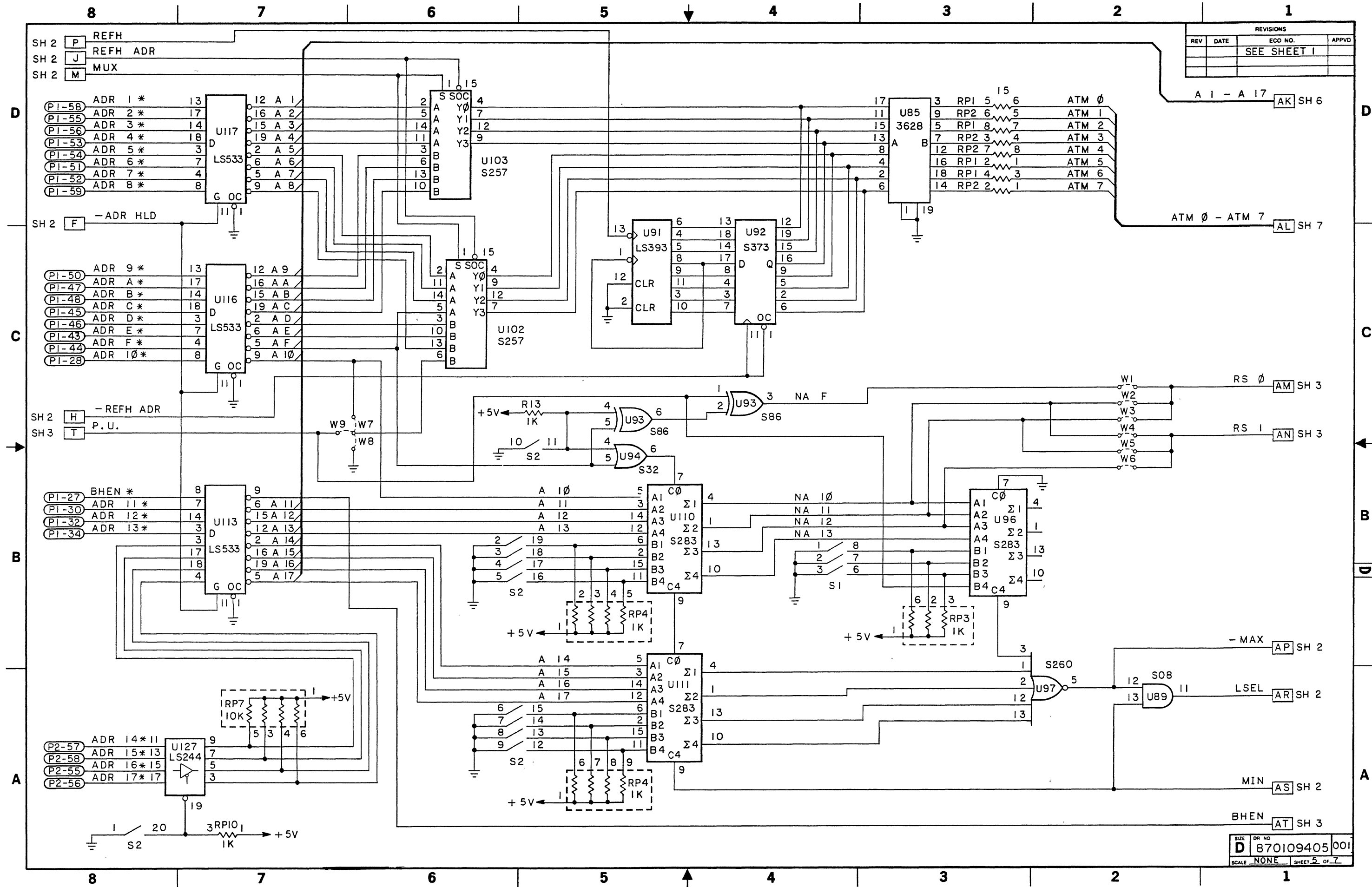
REVISIONS			
REV	DATE	ECO NO.	APPVD
		SEE SHEET 1	



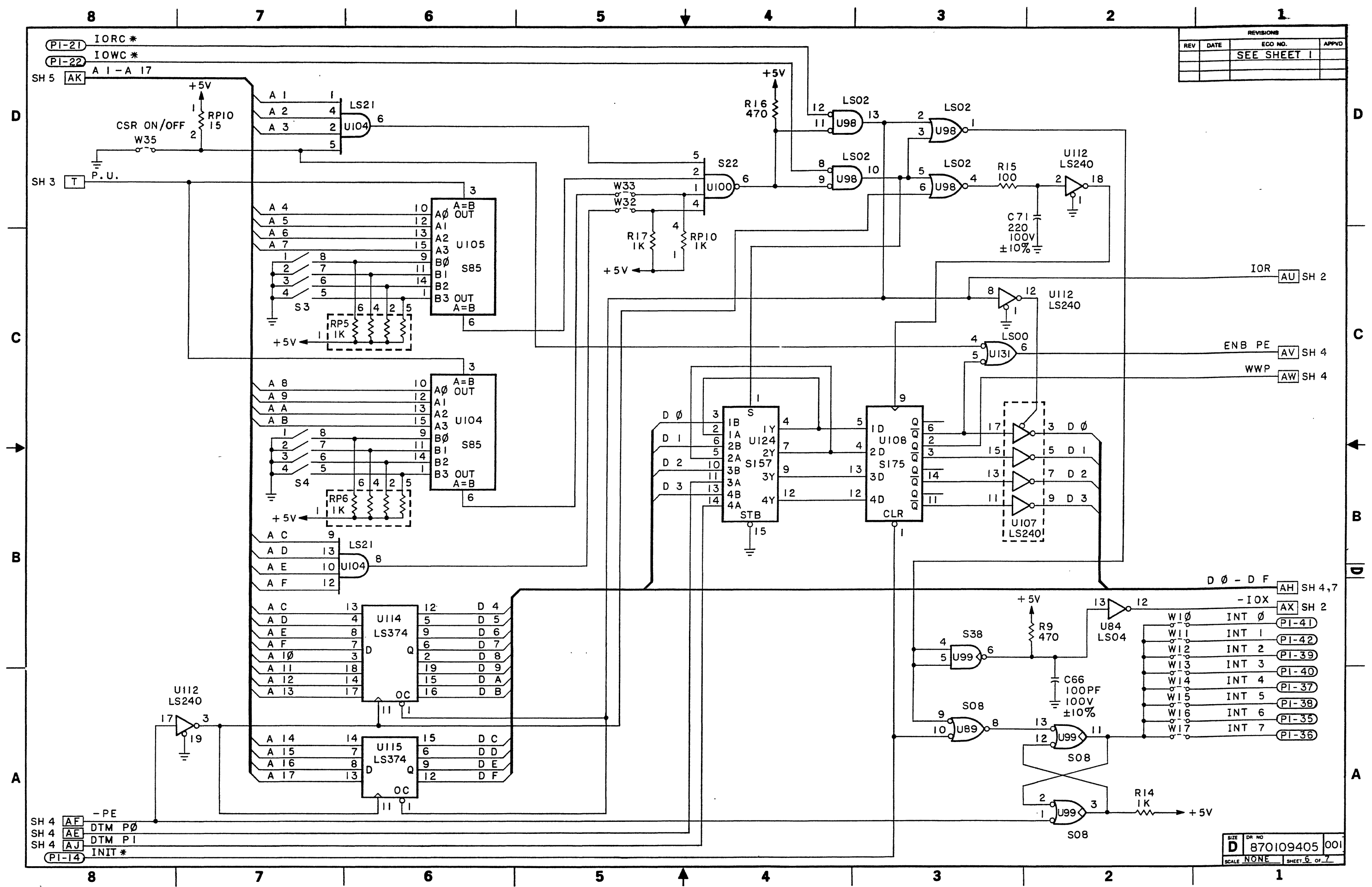
REVISIONS			
REV	DATE	ECO NO.	APPVD
		SEE SHEET 1	



REVISIONS			
REV	DATE	ECO NO.	APPVD
		SEE SHEET 1	



REVISIONS			
REV	DATE	ECO NO.	APPVD
		SEE SHEET 1	

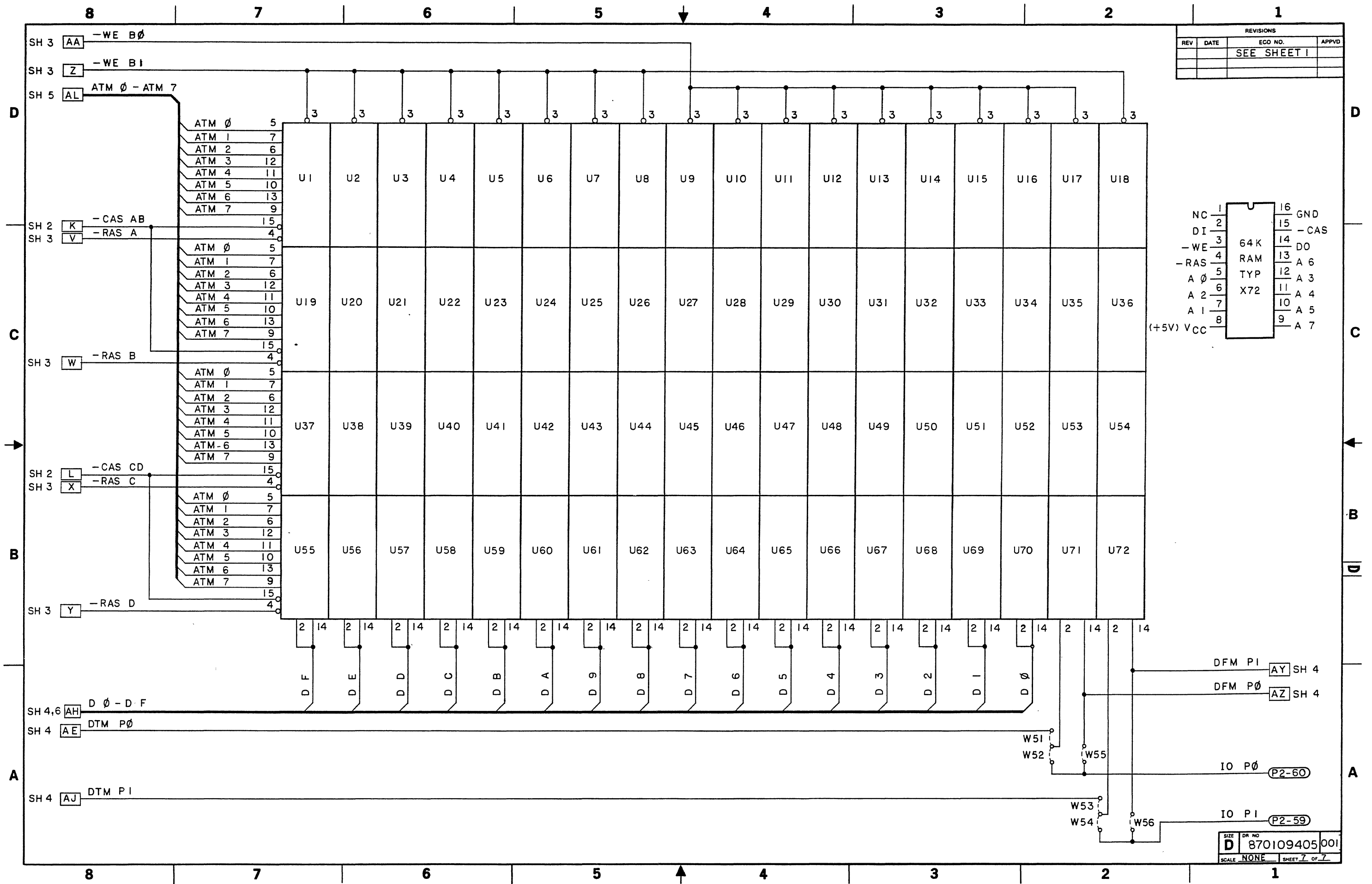


PI-21 IORC \*  
 PI-22 IOWC \*  
 SH 5 AK A 1 - A 17

SH 3 T P. U.

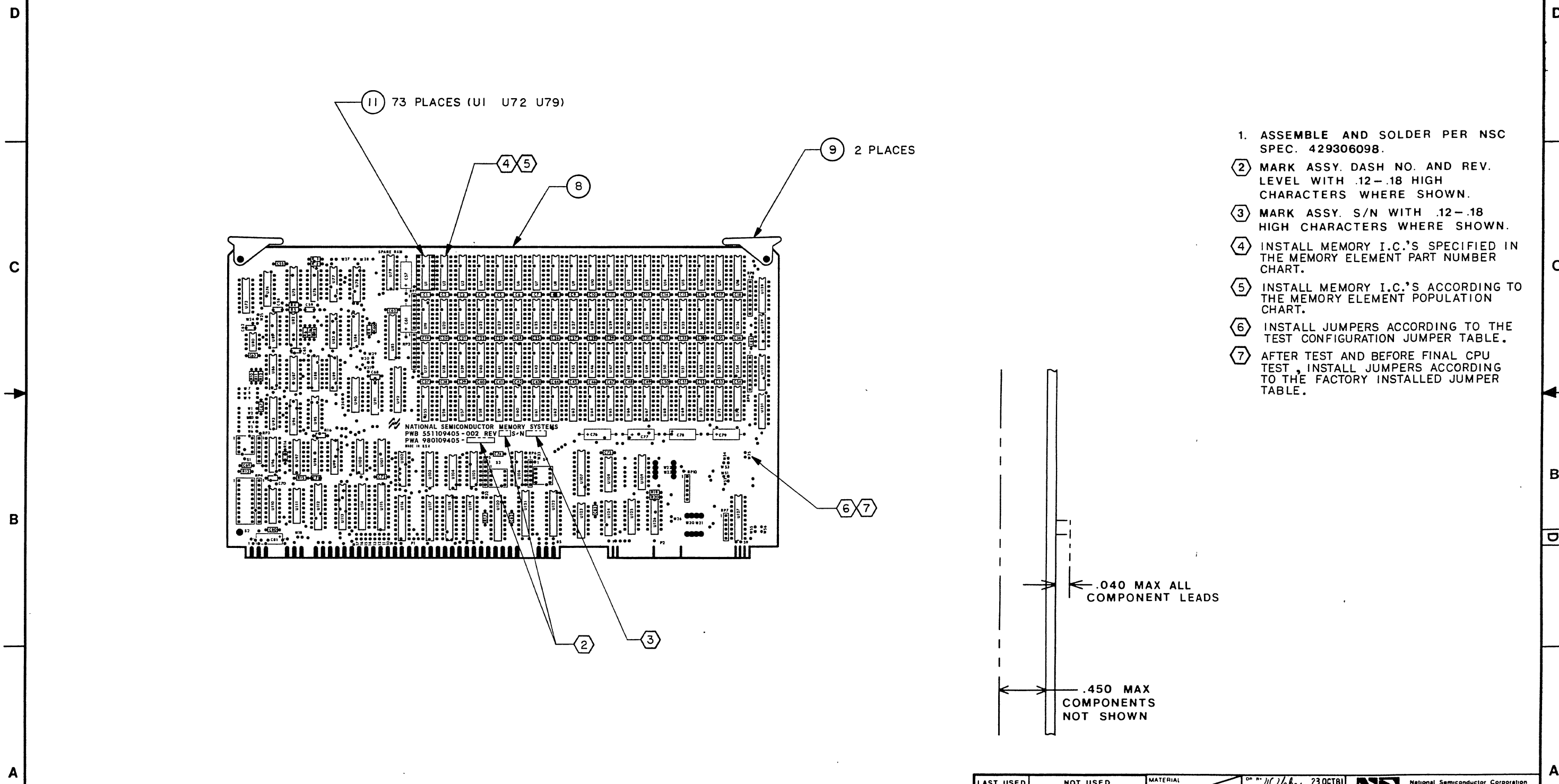
SH 4 AF - PE  
 SH 4 AE DTM P0  
 SH 4 AJ DTM P1  
 PI-14 INIT \*

D 0 - D F AH SH 4,7  
 - IOX AX SH 2  
 W10 INT 0 PI-41  
 W11 INT 1 PI-42  
 W12 INT 2 PI-39  
 W13 INT 3 PI-40  
 W14 INT 4 PI-37  
 W15 INT 5 PI-38  
 W16 INT 6 PI-35  
 W17 INT 7 PI-36



8 7 6 5 4 3 2 1

REVISIONS			
REV	DATE	ECO NO	APPVD
A		PCO 24158	
B	10-24-71	PCO 24161	<i>[Signature]</i>



1. ASSEMBLE AND SOLDER PER NSC SPEC. 429306098.
2. MARK ASSY. DASH NO. AND REV. LEVEL WITH  $.12 - .18$  HIGH CHARACTERS WHERE SHOWN.
3. MARK ASSY. S/N WITH  $.12 - .18$  HIGH CHARACTERS WHERE SHOWN.
4. INSTALL MEMORY I.C.'S SPECIFIED IN THE MEMORY ELEMENT PART NUMBER CHART.
5. INSTALL MEMORY I.C.'S ACCORDING TO THE MEMORY ELEMENT POPULATION CHART.
6. INSTALL JUMPERS ACCORDING TO THE TEST CONFIGURATION JUMPER TABLE.
7. AFTER TEST AND BEFORE FINAL CPU TEST, INSTALL JUMPERS ACCORDING TO THE FACTORY INSTALLED JUMPER TABLE.

11 73 PLACES (U1 U72 U79)

4 5

8

9 2 PLACES

6 7

2

3

NATIONAL SEMICONDUCTOR MEMORY SYSTEMS  
 PWB 551109405-002 REV 1 S-N  
 PWA 980109405

LAST USED		NOT USED		MATERIAL	DR BY: <i>W. J. Baker</i> 23 OCT 81	National Semiconductor Corporation 7900 Semiconductor Drive Santa Clara, Calif. 95051
C84		C64, 73				
R20				FINISH	PWB ASSEMBLY DRAWING	
RP10					BLC 0512	
S4					SIZE DR. NO. D 980109405 000	
U131				TOLERANCE	SCALE 1:1 SHEET 1 OF 3	
				ANG 7 PL 3 PL		

8 7 6 5 4 3 2 1

8

7

6

5

4

3

2

1

④ MEMORY ELEMENT PART NUMBER CHART		
VERSION	ITEM FIND NUMBER	DESCRIPTION
-00Z	89	64K X 1 , DRAM , CERAMIC , 200NS
-01Z *	90	32K X 1 , DRAM , CERAMIC , 200NS , UPPER
-02Z *	91	32K X 1 , DRAM , CERAMIC , 200NS , LOWER
-03Z *	92	16K X 1 , DRAM , CERAMIC , 200NS
-50Z	93	64K X 1 , DRAM , PLASTIC , 200NS
-51Z *	94	32K X 1 , DRAM , PLASTIC , 200NS , UPPER
-52Z *	95	32K X 1 , DRAM , PLASTIC , 200NS , LOWER
-53Z *	96	16K X 1 , DRAM , PLASTIC , 200NS
-04Z		
-05Z		
-06Z		
-07Z		
-54Z		
-55Z		
-56Z		
-57Z		

\* PLANNED FUTURE PRODUCT.

DASH NUMBER DEFINITIONS - REFERENCE ONLY - XYZ		
X	Y	Z
0 = CERAMIC RAM 5 = PLASTIC RAM	0 = 64K RAM , 200NS 1 = 32K RAM , 200NS , UPPER 2 = 32K RAM , 200NS , LOWER 3 = 16K RAM , 200NS	0 = UNPOPULATED 1 = 512K WITH PARITY 2 = 384K WITH PARITY 3 = 256K WITH PARITY 4 = 128K WITH PARITY 5 = 512K W/O PARITY 6 = 384K W/O PARITY 7 = 256K W/O PARITY 8 = 128K W/O PARITY

REVISIONS			
REV	DATE	ECO NO.	APPVD
		SEE SHEET 1	

⑤ MEMORY ELEMENT POPULATION CHART

VERSION	INSTALL LOCATIONS			NOTES
	-00Z , -50Z	-01Z , -02Z , -51Z , -52Z	-03Z , -53Z	
-XY0	NONE	NONE	NONE	UNPOPULATED
-XY1	U1 - U72 , U79	N/A	N/A	512K BYTE WITH PARITY
-XY2	U1 - U54 , U79	N/A	N/A	384K BYTE WITH PARITY
-XY3	U1 - U36 , U79	U1 - U72 , U79	N/A	256K BYTE WITH PARITY
-XY4	U1 - U18 , U79	U1 - U36 , U79	U1 - U72 , U79	128K BYTE WITH PARITY
-XY5	U1 - U16 , U19 - U34 , U37 - U52 , U55 - U70 , U79	N/A	N/A	512K BYTE W/O PARITY
-XY6	U1 - U16 , U19 - U34 , U37 - U52 , U79	N/A	N/A	384K BYTE W/O PARITY
-XY7	U1 - U16 , U19 - U34 , U79	U1 - U16 , U19 - U34 , U37 - U52 , U55 - U70 , U79	N/A	256K BYTE W/O PARITY
-XY8	U1 - U16 , U79	U1 - U16 , U19 - U34 , U79	U1 - U16 , U19 - U34 , U37 - U52 , U55 - U70 , U79	128K BYTE W/O PARITY

8

7

6

5

4

3

2

1

REVISIONS			
REV	DATE	ECO NO.	APPVD
		SEE SHEET 1	

⑥ TEST CONFIGURATION JUMPER TABLE

VERSION	INSTALL	ITEM FIND NUMBER	REMOVE
-X0Z	W3 W6 , W7 , W27	14	W1 , W2 , W4 , W5 , W8 , W9 , W28
-X1Z	W2 , W5 , W9 , W27	14	W1 , W3 , W4 , W6 - W8 , W28
-X2Z	W2 , W5 , W8 , W27	14	W1 , W3 , W4 , W6 , W7 , W9 , W28
-X3Z	W1 , W4 , W7 , W27	14	W2 , W3 , W5 , W6 , W8 , W9 , W28
-X4Z	W3 , W6 , W7 , W28	14	W1 , W2 , W4 , W5 , W8 , W9 , W27
-X5Z	W2 , W5 , W9 , W28	14	W1 , W3 , W4 , W6 - W8 , W27
-X6Z	W2 , W5 , W8 , W28	14	W1 , W3 , W4 , W6 , W7 , W9 , W27
-X7Z	W1 , W4 , W7 , W28	14	W2 , W3 , W5 , W6 , W8 , W9 , W27
ALL	W10 , W18 , W24 , W29 , W32 , W34 , W52 , W54 - W56	13	W11 - W17 , W20 , W21 , W25 , W26 , W30 , W31 , W35 , W51 , W53
ALL	W22 , W23 , W33	14	

⑦ FACTORY INSTALLED JUMPER TABLE

VERSION	INSTALL	ITEM FIND NUMBER	REMOVE
-X0Z	W3 , W6 , W7 W27	14	W1 , W2 , W4 , W5 , W8 , W9 , W28
-X1Z	W2 , W5 , W9 , W27	14	W1 , W3 , W4 , W6 - W8 , W28
-X2Z	W2 , W5 , W8 , W27	14	W1 , W3 , W4 , W6 , W7 , W9 , W28
-X3Z	W1 , W4 , W7 , W27	14	W2 , W3 , W5 , W6 , W8 , W9 , W28
-X4Z	W3 , W6 , W7 , W28	14	W1 , W2 , W4 , W5 , W8 , W9 , W27
-X5Z	W2 , W5 , W9 , W28	14	W1 , W3 , W4 , W6 - W8 , W27
-X6Z	W2 , W5 , W8 , W28	14	W1 , W3 , W4 , W6 , W7 , W9 , W27
-X7Z	W1 , W4 , W7 , W28	14	W2 , W3 , W5 , W6 , W8 , W9 , W27
ALL	W18 , W24 , W29 , W32 , W33 , W51 , W53	13	W10 - W17 , W20 , W21 , W25 , W26 , W30 , W31 , W34 , W35 , W52 , W54 - W56
ALL	W22 , W23	14	



ITEM FIND NO	QUANTITY PER ASSEMBLY				UNIT OF MEAS	EA: EACH OF = IN.:INCH FT.:FEET	BK: BULK AR: AS REQ'D	BILL OF MATERIALS NO.		
	980109405-000							DESCRIPTION	REF DESIGNATOR	
1					000					
2					REF	8701109405-001		SCHEMATIC DIAGRAM		
3					REF	4271109405-001		TEST PROCEDURE		
4					REF	4201109405-001		TECHNICAL MANUAL		
5										
6										
7										
8					1 EA	5511109405-002		PC BOARD		
9					2 EA	740003058-001		CARD EJECTOR		
10										
11					73 EA	214102685-003		SOCKET 16 POS	U1-U72, U79	
12					43 EA	283101551-001		W/W PIN	W10-17, 24-26, 27, 28, 29	
13					6 EA	214101550-001		W/W JUMPER	NOTE 6	
14					4 EA	601002749-001		JUMPER, INSULATED	NOTE 6	
15										
16					3 EA	513107003-004		DIP SWITCH 4 POS	S1, 3, 4	
17					1 EA	513107003-010		DIP SWITCH 10 POS	S2	
18										
19										
20										
21										
22										
REV					A		B		NOTES:	
ENG CHG					24158		24161		TITLE	
DATE					10-21		10-21		BLC 0512	
APPR					<i>[Signature]</i>		<i>[Signature]</i>			
PREPARED BY					CHECKED BY		APPROVED BY		NATIONAL SEMICONDUCTOR CORPORATION	
DATE					DATE		DATE		2900 SEMICONDUCTOR DRIVE SANTA CLARA, CALIF. 95051	
					A		980109405-000		SH 1 OF 5	

ITEM FIND NO	QUANTITY PER ASSEMBLY				UNIT OF MEAS	EA: EACH OF = IN.:INCH FT.:FEET	BK: BULK AR: AS REQ'D	BILL OF MATERIALS NO.		
	980109405-000							DESCRIPTION	REF DESIGNATOR	
23					000					
24					1 EA	482000311-001		IC 74S139	U73	
25					3 EA	482000354-001		IC 74LS00	U74, 123, 131	
26					3 EA	482100777-001		IC 74S37	U75, 123, 130	
27					1 EA	611101027-200		DELAY LINE 200NS	U76	
28					2 EA	482100785-001		IC 74LS04	U77, 84	
29					1 EA	482000785-001		IC 74S04	U78	
30					1 EA	482102160-001		IC 555	U80	
31					1 EA	482100365-001		IC 74LS74	U81	
32					1 EA	482100840-001		IC 74S132	U82	
33					1 EA	482000334-001		IC 74S02	U83	
34					1 EA	482107006-001		IC 3628	U85	
35					1 EA	482107018-001		IC 74LS279	U86	
36					3 EA	482000079-001		IC 74S00	U87, 125, 126	
37					2 EA	482001344-001		IC 74S10	U88, 95	
38					1 EA	482100672-001		IC 74S08	U89	
39					1 EA	482000283-001		IC 8098	U90	
40					1 EA	482102639-001		IC 74LS393	U91	
41					1 EA	482101837-001		IC 74S374	U92	
42					1 EA	482000300-001		IC 74S86	U93	
43					1 EA	482101026-001		IC 74S32	U94	
44					3 EA	482102505-001		IC 74S283	U96, 110, 111	
REV									NOTES:	
ENG CHG					SEE SHEET 1				TITLE	
DATE									BLC 0512	
APPR										
PREPARED BY					CHECKED BY		APPROVED BY		NATIONAL SEMICONDUCTOR CORPORATION	
DATE					DATE		DATE		2900 SEMICONDUCTOR DRIVE SANTA CLARA, CALIF. 95051	
					A		980109405-000		SH 2 OF 5	

ITEM FIND NO	QUANTITY PER ASSEMBLY				UNIT OF MEAS	EA: EACH OF = IN.:INCH FT.:FEET	BK: BULK AR: AS REQ'D	BILL OF MATERIALS NO.		
	980109405-000							DESCRIPTION	REF DESIGNATOR	
45					1 EA	482101177-001		IC 74S260	U97	
46					1 EA	482101381-001		IC 74LS02	U98	
47					1 EA	482100778-001		IC 74S38	U99	
48					1 EA	482000438-001		IC 74S22	U100	
49					2 EA	482000342-001		IC 74S280	U101, 123	
50					2 EA	482101172-001		IC 74S257	U102, 103	
51					1 EA	482107045-001		IC 74LS21	U104	
52					2 EA	482107063-001		IC 74S85	U105, 106	
53					2 EA	482103984-001		IC 74LS240	U107, 112	
54					1 EA	482000437-001		IC 74S175	U108	
55					3 EA	482107061-001		IC 74LS533	U113, 116, 117	
56					2 EA	482107046-001		IC 74LS374	U114, 115	
57					2 EA	482103947-001		IC 74LS373	U118, 122	
58					3 EA	482107062-001		IC 74LS640	U119, 120, 121	
59					1 EA	482000302-001		IC 74S157	U124	
60					1 EA	482103982-001		IC 74LS244	U127	
61										
62										
63										
64										
65										
66										
REV									NOTES:	
ENG CHG					SEE SHEET 1				TITLE	
DATE									BLC 0512	
APPR										
PREPARED BY					CHECKED BY		APPROVED BY		NATIONAL SEMICONDUCTOR CORPORATION	
DATE					DATE		DATE		2900 SEMICONDUCTOR DRIVE SANTA CLARA, CALIF. 95051	
					A		980109405-000		SH 3 OF 5	

ITEM FIND NO	QUANTITY PER ASSEMBLY				UNIT OF MEAS	EA: EACH OF = IN.:INCH FT.:FEET	BK: BULK AR: AS REQ'D	BILL OF MATERIALS NO.		
	980109405-000							DESCRIPTION	REF DESIGNATOR	
67					4 EA	474107002-001		RES. SIP 15Ω / 8	RP1, 2, 8, 9	
68					4 EA	474100806-004		RES. SIP 1KΩ / 6	RP3, 5, 6, 10	
69					1 EA	474107036-102		RES. SIP 1KΩ / 10	RP4	
70					1 EA	474100806-066		RES. SIP 10KΩ / 6	RP7	
71					2 EA	470101134-047		RES. CC. 220Ω	R1, 2	
72					4 EA	470101134-039		RES. CC. 100Ω	R4, 5, 10, 15	
73					1 EA	470101134-077		RES. CC. 3.9KΩ	R6	
74					1 EA	470101134-073		RES. CC. 2.7KΩ	R7	
75					1 EA	470101134-025		RES. CC. 27Ω	R8	
76					2 EA	470101134-055		RES. CC. 470Ω	R9, 16	
77					1 EA	470101134-107		RES. CC. 68KΩ	R11	
78					1 EA	470101134-097		RES. CC. 27KΩ	R12	
79					3 EA	470101134-063		RES. CC. 1KΩ	R13, 14, 17	
80										
81					27 EA	151104975-012		CAP. CER. 47UF	SEE BELOW 1	
82					41 EA	151104975-007		CAP. CER. 1UF	SEE BELOW 2	
83					2 EA	151101308-017		CAP. CER 220 PF	C58, 59	
84					6 EA	152107059-004		CAP. ALUM 22UF	C57, 61, 76-79, 81	
85					3 EA	151101308-013		CAP. CER 100 PF	C62, 66, 71	
86					1 EA	151101308-009		CAP. CER. 47 PF	C65	
87										
88										
REV									NOTES:	
ENG CHG					SEE SHEET 1				TITLE	
DATE									BLC 0512	
APPR										
PREPARED BY					CHECKED BY		APPROVED BY		NATIONAL SEMICONDUCTOR CORPORATION	
DATE					DATE		DATE		2900 SEMICONDUCTOR DRIVE SANTA CLARA, CALIF. 95051	
					A		980109405-000		SH 4 OF 5	

ITEM FIND NO	QUANTITY PER ASSEMBLY				UNIT OF MEAS	EA: EACH OF = IN.:INCH FT.:FEET	BK: BULK AR: AS REQ'D	BILL OF MATERIALS NO.		
	980109405-000							DESCRIPTION	REF DESIGNATOR	
89					0 EA	482107076-002		64KX1 DRAM, CER. 200 NS	NOTE 4, 5	
90								32KX1 DRAM, U, CER. 200 NS	NOTE 4, 5 *	
91								32KX1 DRAM, L, CER. 200 NS	NOTE 4, 5 *	
92								16KX1 DRAM, CER. 200 NS	NOTE 4, 5 *	
93					0 EA	482107076-012		64KX1 DRAM, PLTIC. 200 NS	NOTE 4, 5	
94								32KX1 DRAM, U, PLTIC. 200 NS	NOTE 4, 5 *	
95								32KX1 DRAM, L, PLTIC. 200 NS	NOTE 4, 5 *	
96								16KX1 DRAM, PLTIC. 200NS	NOTE 4, 5 *	
97										
98										
99										
100										
101										
102										
103										
104										
105										
106										
107										
108										
109										
110										
REV									NOTES:	
ENG CHG					SEE SHEET 1				TITLE	
DATE									*PLANNED FUTURE PRODUCT. BLC 0512	
APPR										
PREPARED BY					CHECKED BY		APPROVED BY		NATIONAL SEMICONDUCTOR CORPORATION	
DATE					DATE		DATE		2900 SEMICONDUCTOR DRIVE SANTA CLARA, CALIF. 95051	
					A		980109405-000		SH 5 OF 5	